



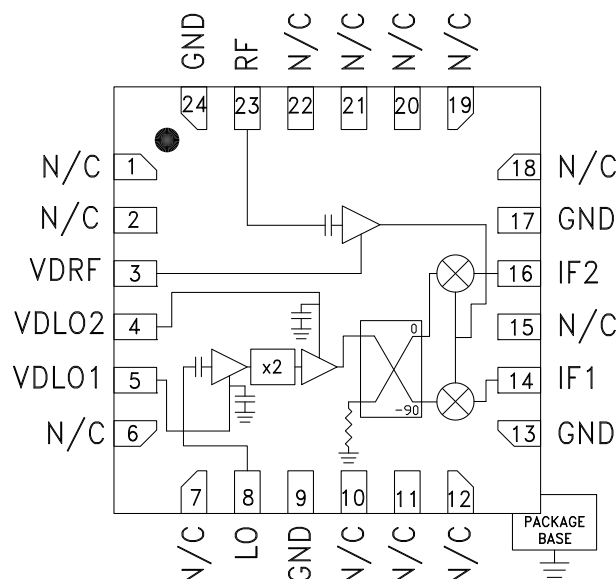
GaAs MMIC I/Q DOWNCONVERTER 17 - 20 GHz

Typical Applications

The HMC966LP4E is ideal for:

- Point-to-Point and Point-to-Multi-Point Radio
- Military Radar, EW & ELINT
- Satellite Communications

Functional Diagram



Features

- Conversion Gain: 14 dB
- Image Rejection: 40 dBc
- 2 LO to RF Isolation: 40 dB
- Noise Figure: 2.5 dB
- Input IP3: 0 dBm
- 24 Lead 4X4 mm SMT Package: 16mm²

General Description

The HMC966LP4E is a compact GaAs MMIC I/Q downconverter in a leadless RoHS compliant SMT package. This device provides a small signal conversion gain of 14 dB with a noise figure of 2.5 dB and 40 dBc of image rejection across the frequency band. The HMC966LP4E utilizes an LNA followed by an image reject mixer which is driven by an active x2 multiplier. The image reject mixer eliminates the need for a filter following the LNA, and removes thermal noise at the image frequency. I and Q mixer outputs are provided and an external 90° hybrid is needed to select the required sideband. The HMC966LP4E is a much smaller alternative to hybrid style image reject mixer downconverter assemblies, and is compatible with surface mount manufacturing techniques.

Electrical Specifications, $T_A = +25^\circ\text{C}$, IF = 1000 MHz, LO = +6 dBm, Vdd = 3.5 Vdc LSB ^[1]

Parameter	Min.	Typ.	Max.	Units
Frequency Range, RF		17 - 20		GHz
Frequency Range, LO		7.5 - 11.75		GHz
Frequency Range, IF		DC - 3.5		GHz
Conversion Gain (As IRM)	10	14		dB
Noise Figure		2.5	3.5	dB
Image Rejection	15	40		dBc
1 dB Compression (Input)		-9		dBm
2 LO to RF Isolation	38	47		dB
2 LO to IF Isolation	9	14		dB
IP3 (Input)	-2	0		dBm
Amplitude Balance ^[2]		0.5		dB
Phase Balance ^[2]		17		deg
Total Supply Current		160	200	mA

[1] Data taken as IRM with external IF 90° Hybrid

[2] Data taken without external 90° hybrid, IF = 1000 MHz

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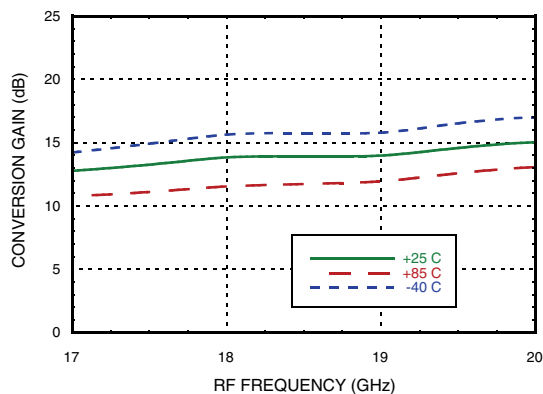
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**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**

Data Taken As IRM With External IF 90° Hybrid, IF = 1000 MHz

Conversion Gain LSB vs. Temperature



Conversion Gain LSB vs. LO Drive

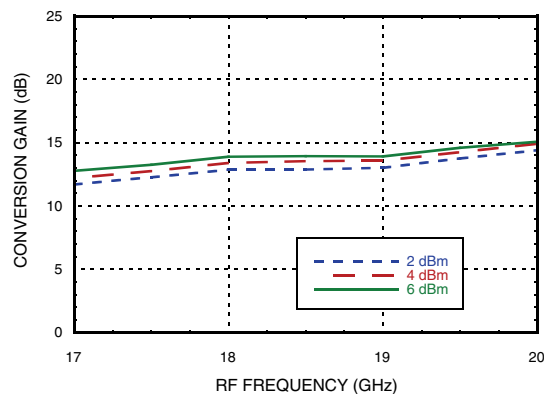
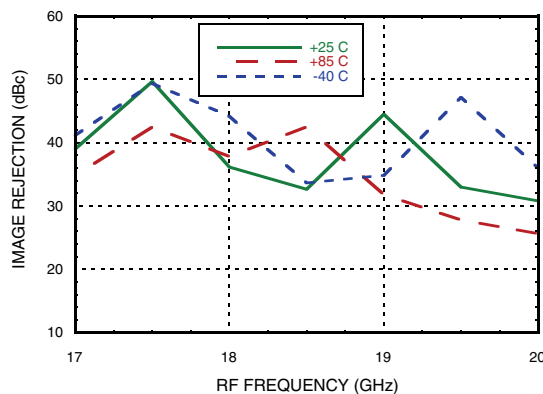
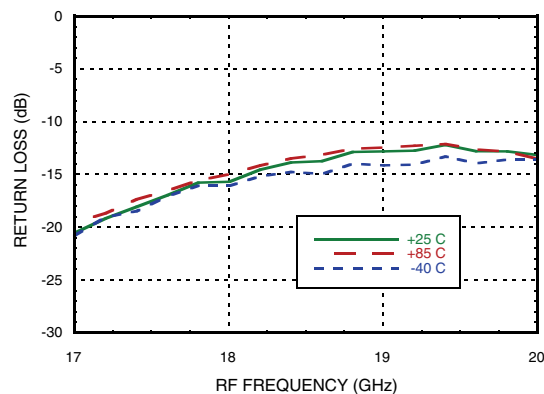


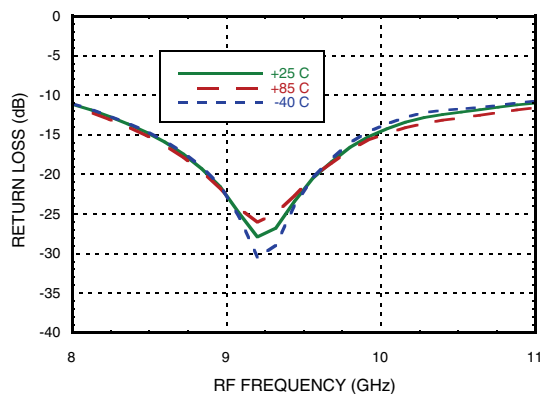
Image Rejection vs. Temperature



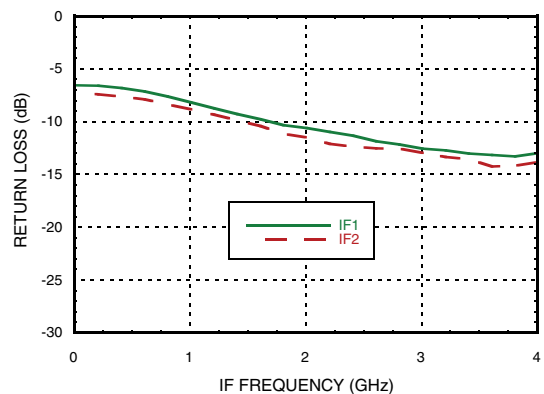
RF Return Loss vs. Temperature



LO Return Loss vs. Temperature



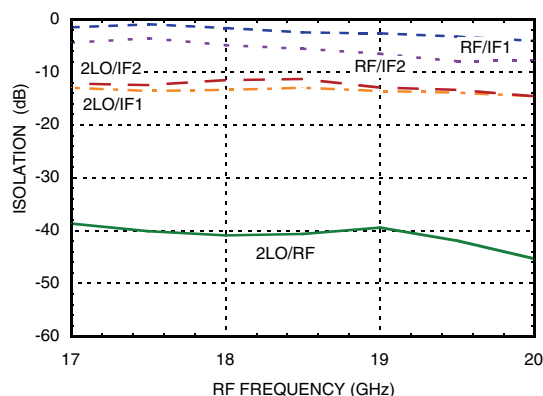
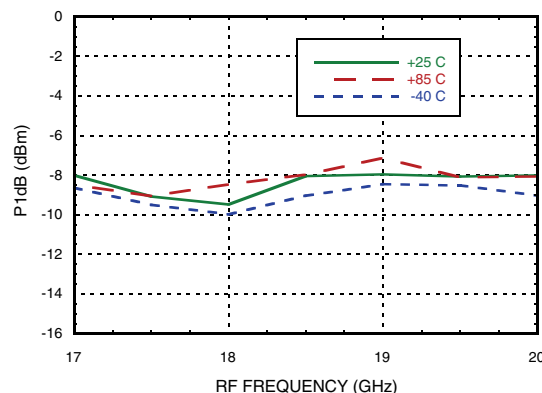
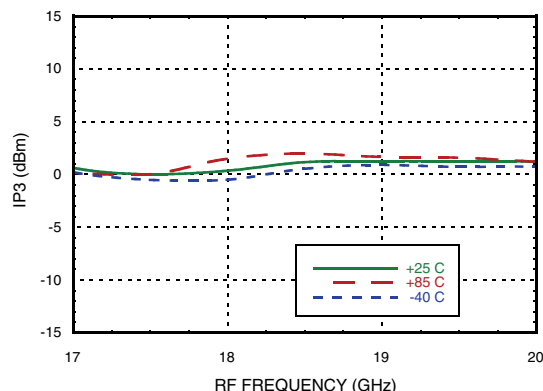
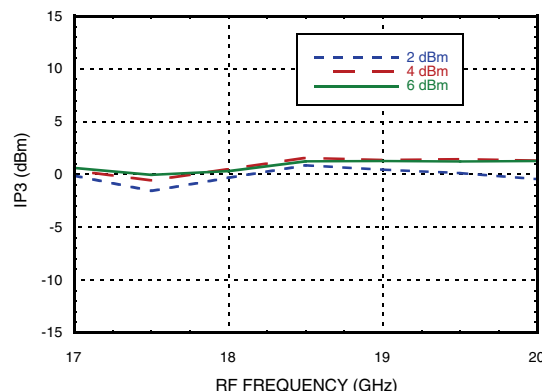
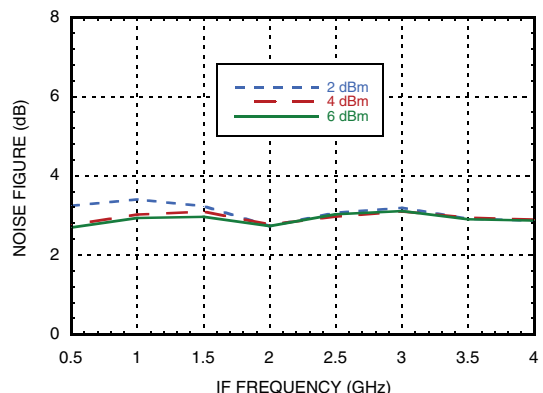
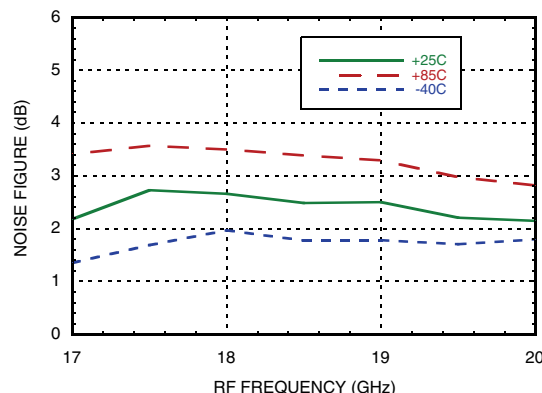
IF Return Loss ^[1]



[1] Data taken without external 90° hybrid.

**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**

Data Taken as IRM With External IF 90° Hybrid, IF = 1000 MHz

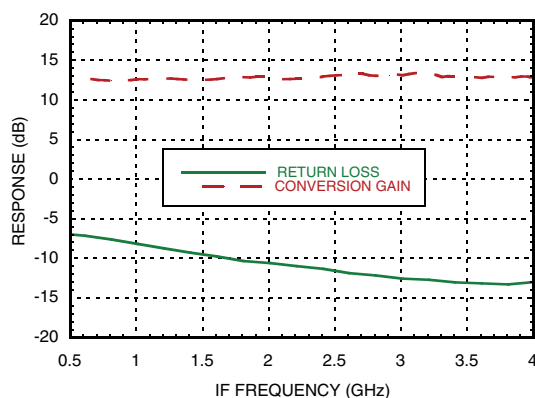
Isolations

Input P1dB LSB vs. Temperature

Input IP3, LSB vs. Temperature

Input IP3, LSB vs. LO Drive

**Noise Figure vs. LO Drive,
LO Frequency = 8.25 GHz**

**Noise Figure vs. Temperature,
IF Frequency = 1000 MHz**




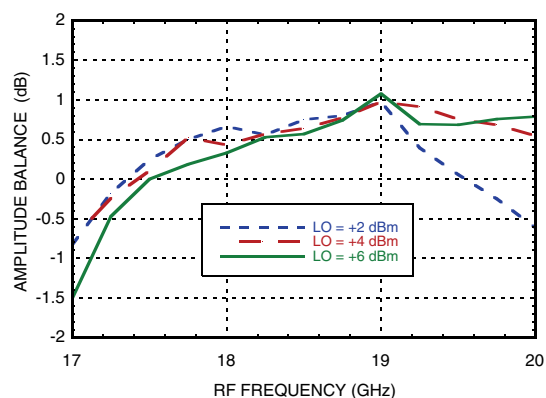
**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**

Quadrature Channel Data Taken Without IF 90° Hybrid, IF = 1000 MHz

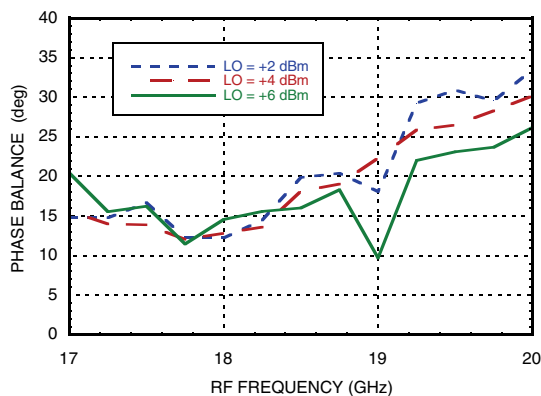
IF Bandwidth ^[1]



Amplitude Balance vs. LO Drive ^[2]



Phase Balance vs. LO Drive ^[2]

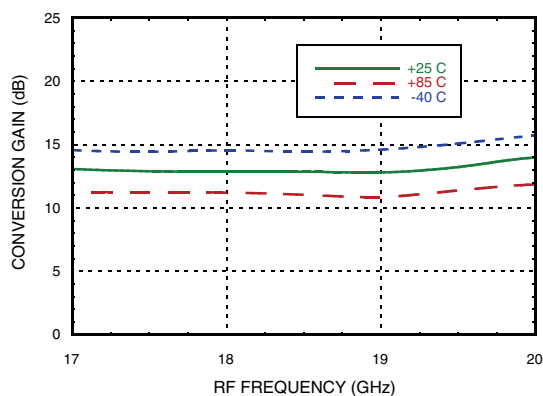
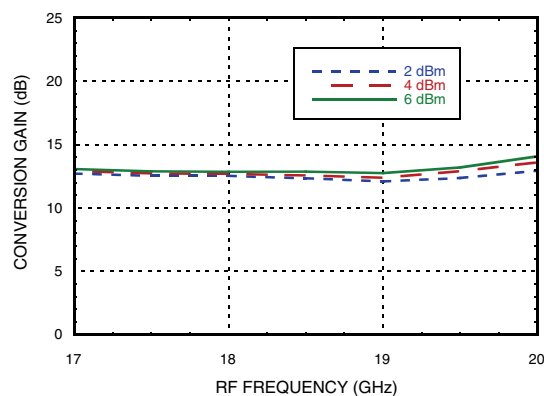
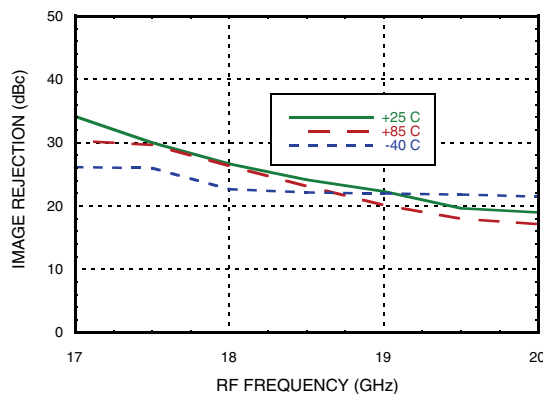
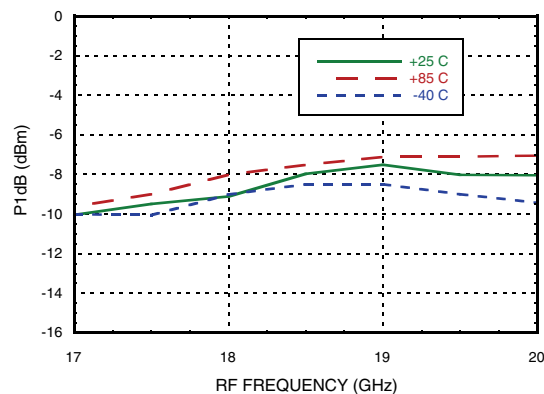
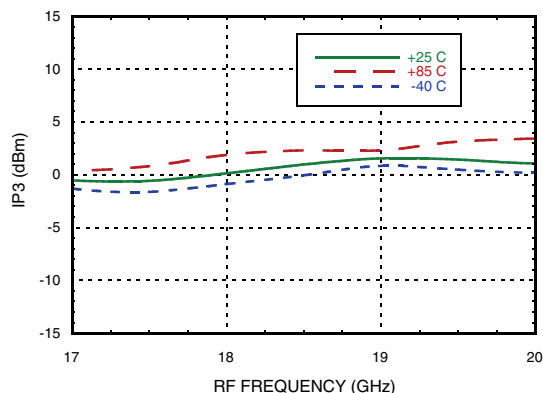
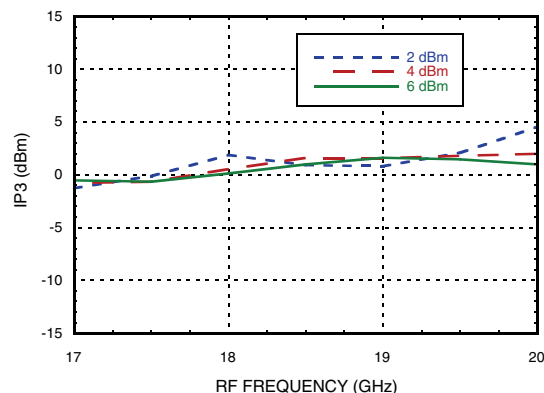


[1] Data taken with LO frequency fixed at 6.5 GHz and RF varied.

[2] Data taken with IF = 1000 MHz


GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz

Data Taken as IRM With External IF 90° Hybrid, IF = 1000 MHz

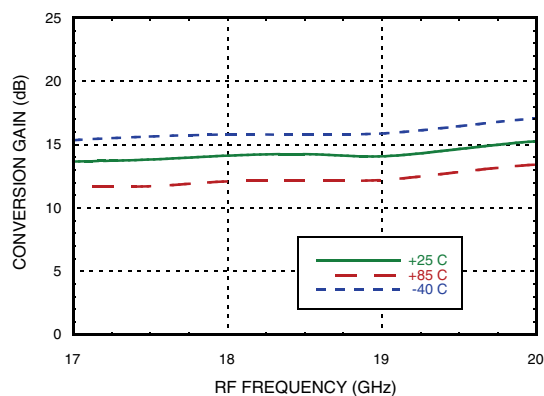
Conversion Gain, USB vs. Temperature

Conversion Gain, USB vs. LO Drive

Image Rejection vs. Temperature

Input P1dB, USB vs. Temperature

Input IP3, USB vs. Temperature

Input IP3, USB vs. LO Drive




**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**

Data Taken as IRM With External IF 90° Hybrid, IF = 2000 MHz

Conversion Gain, LSB vs. Temperature



Conversion Gain, LSB vs. LO Drive

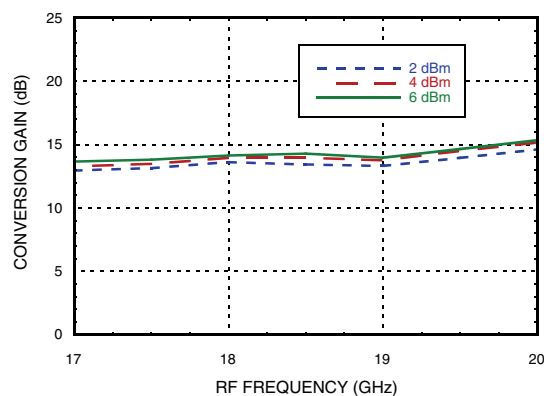
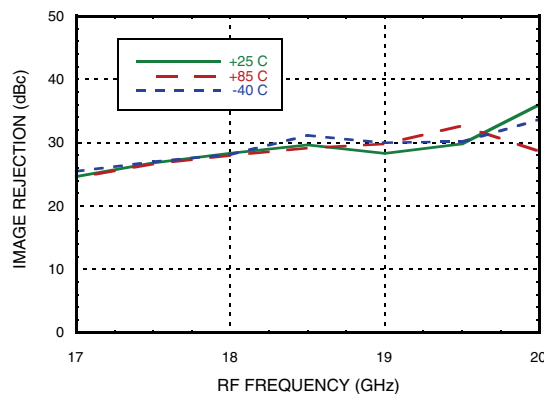
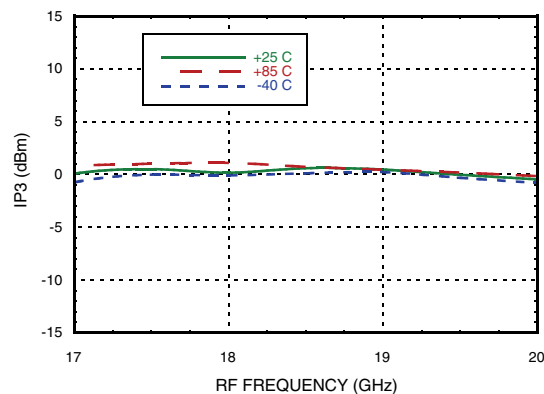


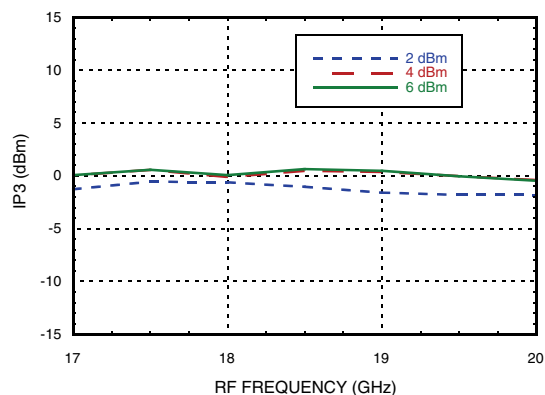
Image Rejection vs. Temperature



Input IP3, LSB vs. Temperature

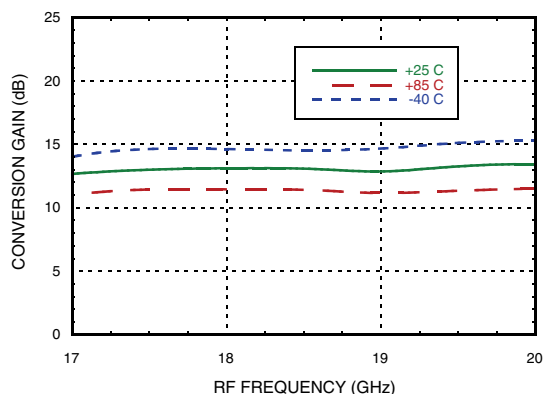
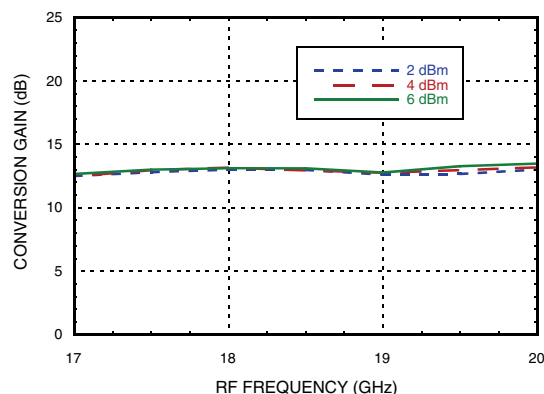
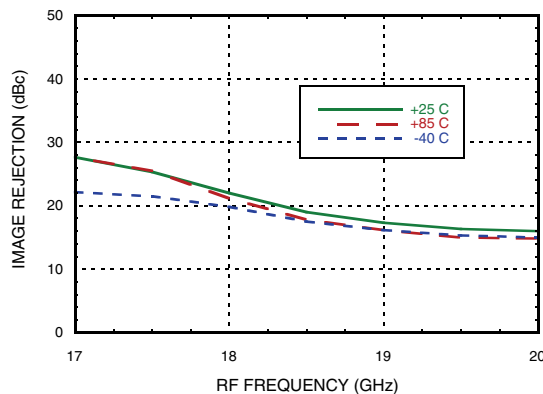
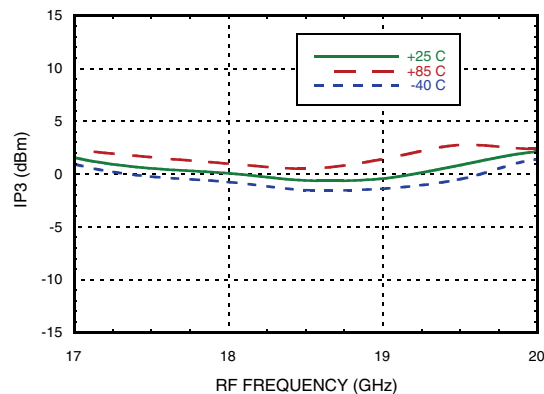
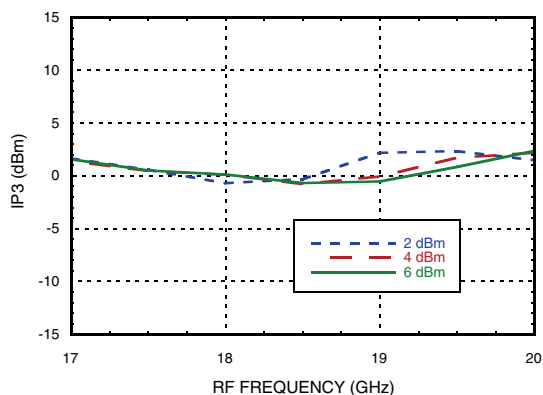


Input IP3, LSB vs. LO Drive




GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz

Data Taken as IRM With External IF 90° Hybrid, IF = 2000 MHz

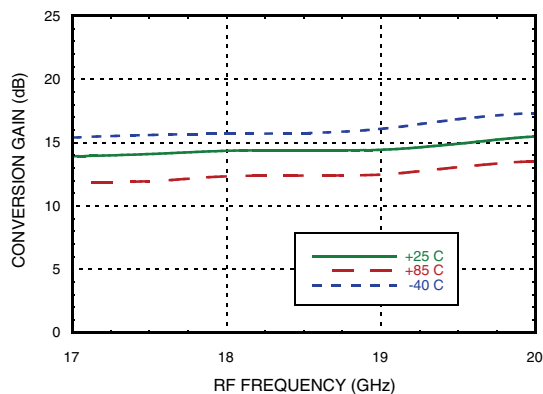
Conversion Gain, USB vs. Temperature

Conversion Gain, USB vs. LO Drive

Image Rejection vs. Temperature

Input IP3, USB vs. Temperature

Input IP3, USB vs. LO Drive




**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**

Data Taken as IRM With External IF 90° Hybrid, IF = 3300 MHz

Conversion Gain, LSB vs. Temperature



Conversion Gain, LSB vs. LO Drive

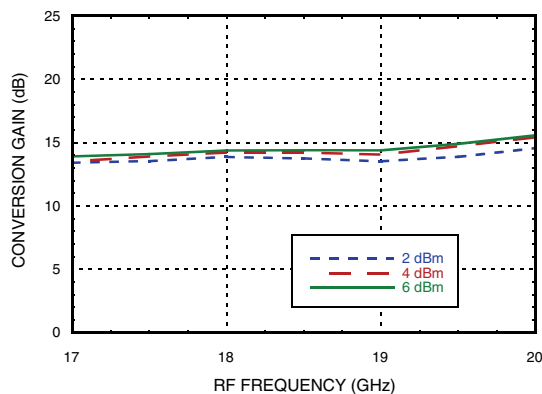
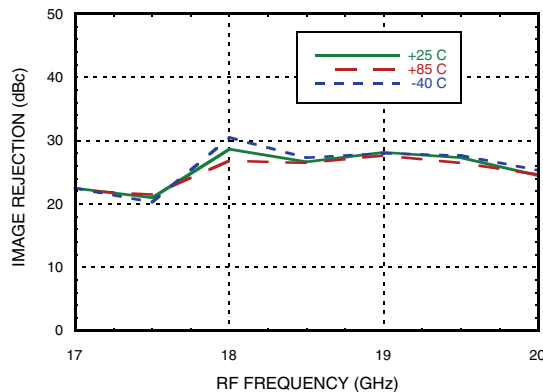
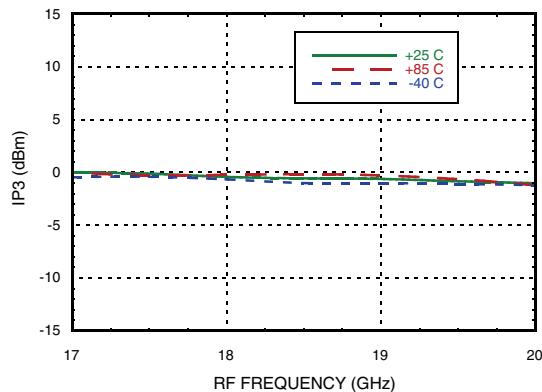


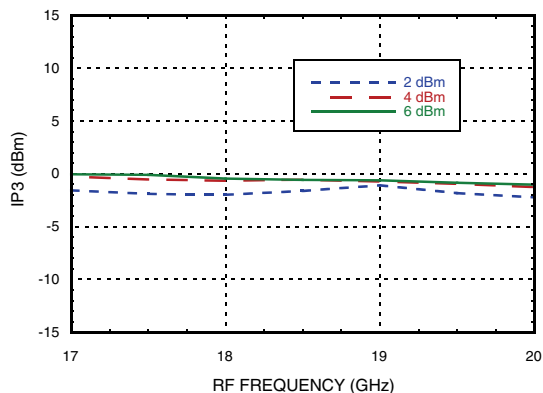
Image Rejection vs. Temperature



Input IP3, LSB vs. Temperature

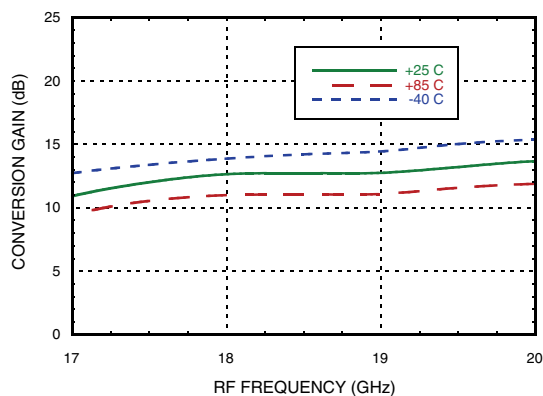
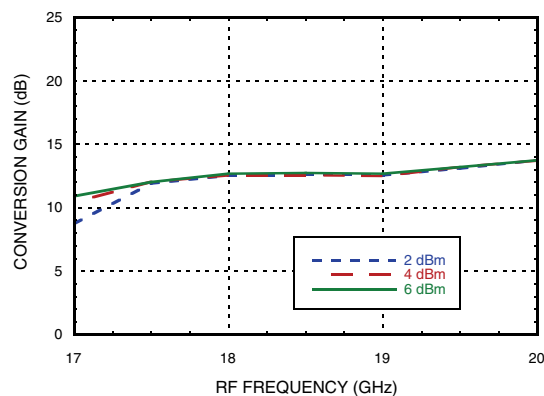
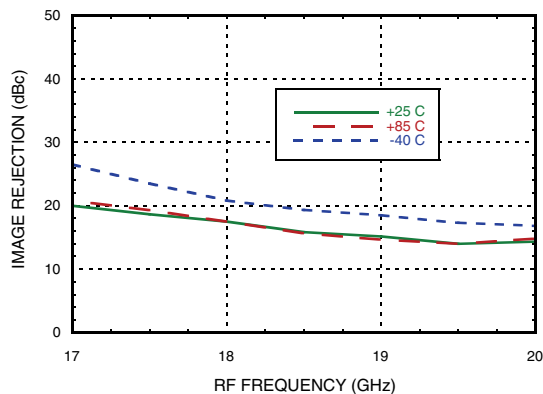
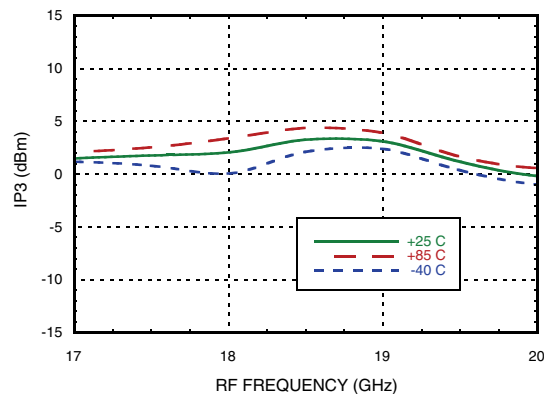
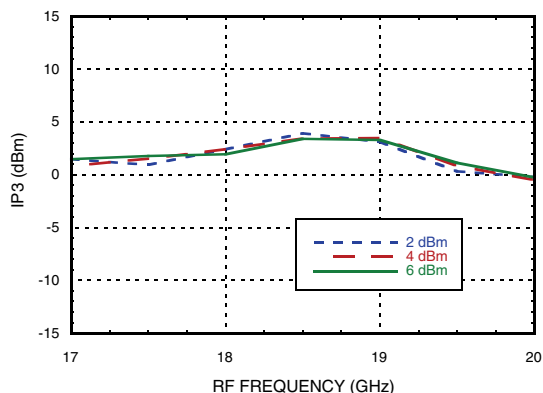


Input IP3, LSB vs. LO Drive




GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz

Data Taken as IRM With External IF 90° Hybrid, IF = 3300 MHz

Conversion Gain, USB vs. Temperature

Conversion Gain, USB vs. LO Drive

Image Rejection vs. Temperature

Input IP3, USB vs. Temperature

Input IP3, USB vs. LO Drive




GAAS MMIC I/Q DOWNCONVERTER 17 - 20 GHz

MxN Spurious Outputs

	nLO				
mRF	0	1	2	3	4
0	x	-12.5	4.6	-18.7	-26.0
1	-10.7	-16.3	0	-16.7	-16
2	-53.4	-67.7	-42.1	-41.5	-39.9
3	x	-99.2	-82.9	-81.8	-73
4	x	x	x	-104.5	-99.1

RF = 18 GHz @ -20 dBm

LO = 8.5 GHz @ +4 dBm

Data taken without IF hybrid

All values in dBc below IF power level (1RF -2LO = 1 GHz)

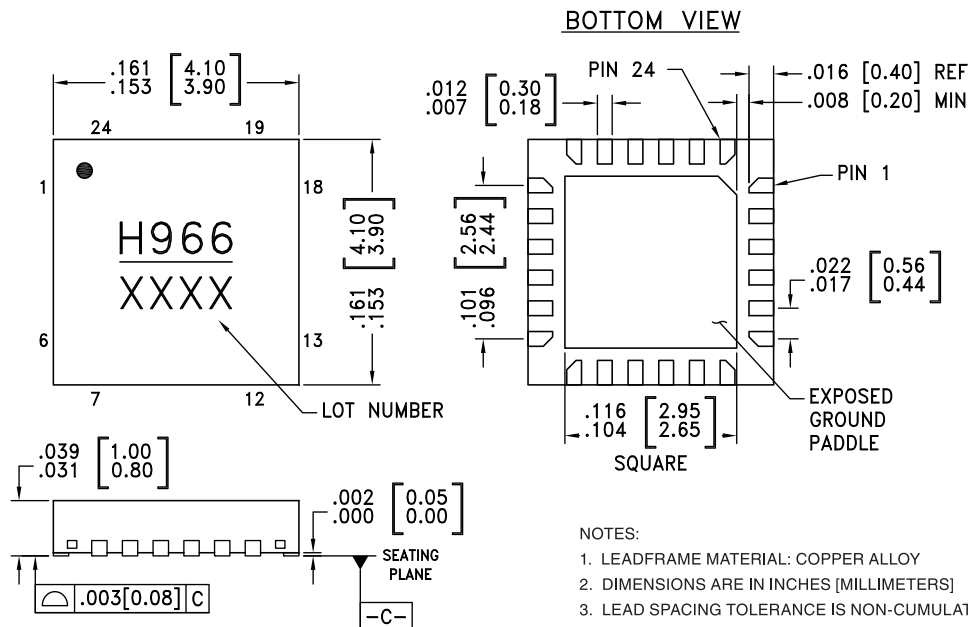
Absolute Maximum Ratings

RF	+10 dBm
LO Drive	+10 dBm
Vdd	4V
Channel Temperature	175 °C
Continuous P _{diss} (T=85°C) (derate 16.4 mW/°C above 85°C)	1.48 W
Thermal Resistance (R _{th}) (channel to package bottom)	60.7 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
ESD Sensitivity (HBM)	Class 0



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[1]
HMC966LP4E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	H966 XXXX

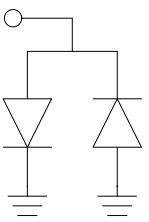
[1] 4-Digit lot number XXXX

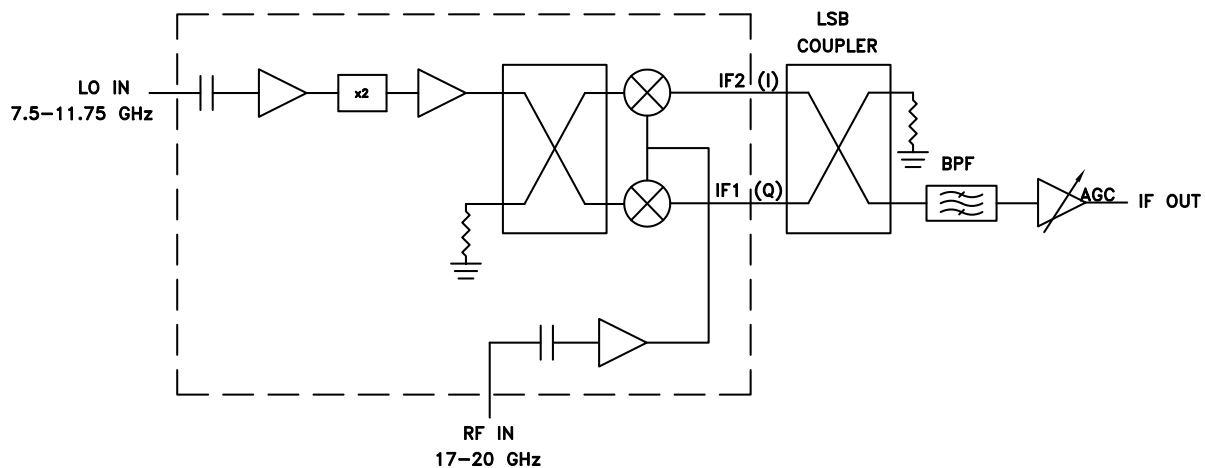
[2] Max peak reflow temperature of 260 °C

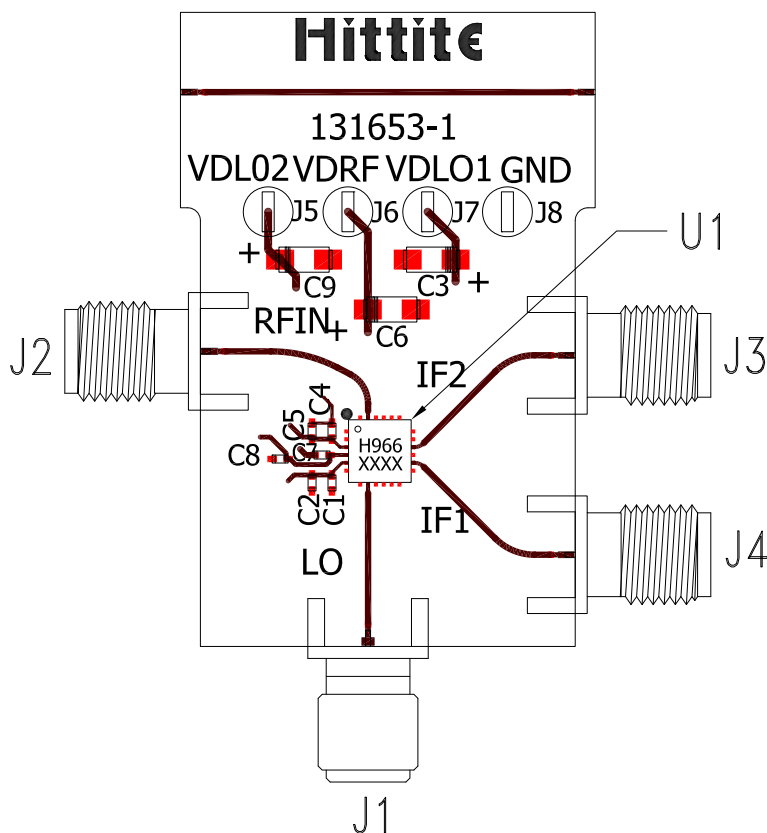
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**GAAS MMIC I/Q DOWNCONVERTER
17 - 20 GHz**
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 6, 7, 10 - 12, 15, 18 - 22	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
3	VDRF	Power supply for RF LNA.	
4	VDLO2	Power supply for second stage of LO amplifier.	VDLO2 
5	VDLO1	Power supply for first stage of LO amplifier.	VDLO1 
8	LO	This pin is AC coupled and matched to 50 Ohms.	LO 
9, 13, 17, 24	GND	These pins and the exposed ground paddle must be connected to RF/DC ground.	GND 
16	IF2	This pin is DC coupled. For applications not requiring operation to DC this port should be DC blocked externally using a series capacitor whose value has been chosen to pass the necessary frequency range. For operation to DC, this pin must not sink / source more than 3 mA of current or part non-function and possible failure will result.	IF1, IF2 
14	IF1		
23	RF	This pin is AC coupled and matched to 50 Ohms	RF 

Typical Application Circuit


Evaluation PCB

List of Materials for Evaluation PCB 131656 ^[1]

Item	Description
J1	PCB Mount SMA RF Connector, SRI
J2, J3	PCB Mount K Connector, SRI
J5 - J8	DC Pin
C1, C4, C7	100 pF Capacitor, 0402 Pkg.
C2, C5, C8	10 nF Capacitor, 0402 Pkg.
C3, C6, C9	4.7 μ F Capacitor, Case A Pkg.
U1	HMC966LP4E
PCB ^[2]	161653 Evaluation Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

Данный компонент на территории Российской Федерации

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9